

IN THE CLAIMS

Please amend the claims as shown in the listing of claims below.

Claims 1-37 (Canceled)

Claim 38. (Currently Amended) A method of making a GaN single crystal substrate in a growth apparatus including a reaction chamber, a gas introducing port, an exhaust port, a resistance heater, and a rotary support member, said method comprising:

placing a GaN single crystal employed as a seed crystal on said rotary support member;
~~an ingot-forming step of~~ forming an ingot of GaN single crystal by growing an epitaxial layer made of GaN on a said GaN single crystal employed as a said seed crystal, while said rotary support member is at a certain distance from said gas introducing port; and
~~a cutting step of~~ cutting said ingot into a plurality of sheets.

Claim 39. (Currently Amended) A method of making a GaN single crystal substrate in a growth apparatus including a reaction chamber, a gas introducing port, an exhaust port, a resistance heater, and a rotary support member, said method comprising:

placing a GaN single crystal employed as a seed crystal on said rotary support member;
~~an ingot-forming step of~~ forming an ingot of GaN single crystal by growing an epitaxial layer made of GaN on a said GaN single crystal employed as a said seed crystal, while said rotary support member is at a certain distance from said gas introducing port; and
~~a cleaving step of~~ cleaving said ingot into a plurality of sheets.

Claims 40-58 (Canceled)

Claim 59 (New) A method of making as GaN single crystal substrate as claimed in claim 38, where said growth apparatus is a vertical furnace and said growing of said epitaxial layer is by HVPE.

Claim 60 (New) A method of making as GaN single crystal substrate as claimed in claim 39, where said growth apparatus is a vertical furnace and said growing of said epitaxial layer is by HVPE.